
(12) **UK Patent Application** (19) **GB** (11) **2 373 497** (13) **A**

(43) Date of Printing by UK Office **25.09.2002**

(21) Application No **0215873.1**

(22) Date of Filing **05.12.2000**

(30) Priority Data

(31) **09458278** (32) **09.12.1999** (33) **US**

(86) International Application Data

PCT/US2000/042555 En 05.12.2000

(87) International Publication Data

WO2001/042163 En 14.06.2001

(51) INT CL⁷

C04B 35/581 41/00 , H01L 21/68

(52) UK CL (Edition T)

C1A AE5G AG4 APC

H1K KMBX

(56) Documents Cited by ISA

EP 0882689 A

EP 0771772 A

WO 1997/035816 A

(58) Field of Search by ISA

INT CL⁷ **C04B , H01L**

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(54) Abstract Title

High-purity low-resistivity electrostatic chucks

(57) The volume resistivity of a body consisting essentially of aluminum nitride is reduced by exposing the body to a soak temperature of at least about 1000°C in an atmosphere deficient in nitrogen, such as an atmosphere consisting essentially of argon. The body can be, for example, a green body of aluminum nitride powder of a densified, or sintered body, such as a polycrystalline body. An electrostatic chuck has an electrode within a chuck body. A first portion of the chuck body, at a first side of the electrode, has a volume resistivity less than about 1×10^{13} ohm.cm at about 23°C. A second portion of the body, at a second side of the electrode, has a volume resistivity within one order of magnitude that of the first portion.

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